



### 12W Hi-Fi AUDIO AMPLIFIER

The TDA 2010 is a monolithic integrated operational amplifier in a 14-lead quad in-line plastic package, inteded for use as a low frequency class B power amplifier. Typically it provides 12W output power (d = 1%) at  $\pm$  14V/4 $\Omega$ ; at V<sub>5</sub> =  $\pm$  14V the guaranteed output power is 10W on a 4 $\Omega$  load and 8W on a 8 $\Omega$  load (DIN norm 45500). The TDA 2010 provides high output current (up to 3.5 A) and has very low harmonic and cross-over distortion. Further, the device incorporates an original (and patented) short circuit protection system, comprising an arrangement for automatically limiting the dissipated power so as to keep to working point of the output transistors within their safe operating area. A conventional thermal shut-down system is also included. The TDA 2010 is pin to pin equivalent to TDA 2020

### **ABSOLUTE MAXIMUM RATINGS**

٧,	Supply voltage		± 18	V
V <sub>i</sub>	Input voltage		V,	
V <sub>i</sub>	Differential input voltage		± 15	V
ام	Output peak current (internally limited)	ł	3.5	Α
$P_{tot}$	Power dissipation at $T_{case} \leq 95^{\circ}C$	İ	18	W
$T_{stg}^{id}, T_{j}$	Storage and junction temperature		-40 to 150	°C
		1		

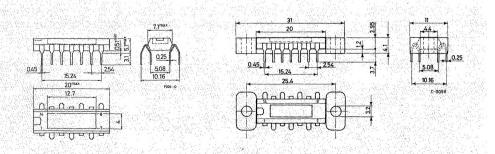
ORDERING NUMERS:

TDA 2010 B82 dual in-line plastic package TDA 2010 B92 quad in-line plastic package

TDA 2010 BC2 dual in-line plastic package with spacer TDA 2010 BD2 quad in-line plastic package with spacer

### MECHANICAL DATA

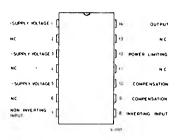
Dimensions in mm



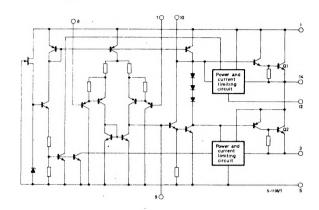


# CONNECTION AND SCHEMATIC DIAGRAMS

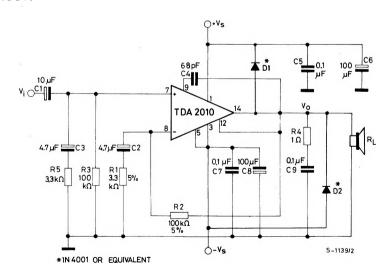
(top view)



The copper slug is electrically connected to pin 5 (substrate)



### **TEST CIRCUIT**



### THERMAL DATA

$R_{\text{th }j\text{-case}}$	Thermal resistance junction-case	max	3	°C/W
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**ELECTRICAL CHARACTERISTICS** (Refer to the test circuit,  $V_s = \pm$  14V,  $T_{amb} = 25^{\circ}$ C unless otherwise specified)

	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>s</sub>	Supply voltage		± 5		± 18	v
Id	Quiescent drain current	V <sub>s</sub> = ± 18V		45		mA
l <sub>b</sub>	Input bias current			0.15		μА
Vos	Input offset voltage	V <sub>s</sub> = ± 17V		5		mV
los	Input offset current	\\ \s\ \s\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\		0.05		μА
Vos	Output offset voltage			10	100	mV
P <sub>o</sub>	Output power	$ d = 1\% $ $ T_{case} \le 70^{\circ} C $ $ f = 40 \text{ to } 15 000 \text{ Hz} $ $ R_{L} = 4 \Omega $ $ R_{L} = 8 \Omega $	10	12 9		ww
				15 12		w
Vi	Input sensitivity	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		220 250		m∨ m∨
В	Frequency response (-3dB)	R <sub>L</sub> = 4 Ω C4 = 68 pF	10 to 160 000			Hz
d	Distortion	$P_{O} = 100 \text{ mW to } 10 \text{ W}$ $R_{L} = 4 \Omega$ $T_{Case} \le 70^{\circ} \text{ C}$ $f = 1 \text{ kHz}$ $f = 40 \text{ to } 15 \text{ 000 Hz}$		0.1 0.3	1	% %
		$P_{o} = 100 \text{ mW to 8 W}$ $R_{L} = 8 \Omega$ $T_{case} \le 70^{\circ} \text{C}$ $f = 1 \text{ kHz}$ $f = 40 \text{ to 15 000 Hz}$		0.1 0.2	1	% %
Ri	Input resistance (pin 7)			5		MΩ
G <sub>v</sub>	Voltage gain (open loop)	D -40 ( 4111		100		dB
G <sub>v</sub>	Voltage gain (closed loop)	$- R_{L} = 4 \Omega \qquad f = 1 \text{ kHz}$	29.5	30	30.5	dB
e <sub>N</sub>	Input noise voltage	R <sub>L</sub> = 4 Ω		4	-	μ∨
iN	Input noise current	B (-3 dB) = 22 Hz to 22 KHz		0.1		nA



### **ELECTRICAL CHARACTERISTICS** (continued)

	Parameter	Test conditions	Min.	Тур.	Max.	Unit
SVR	Supply voltage rejection	$R_{J_{-}} = 4 \Omega$ $f_{ripple} = 100 \text{ Hz}$		50		dB
I <sub>d</sub>	Drain current	$P_{o} = 12 \text{ W} \qquad R_{L} = 4 \Omega$ $P_{o} = 9 \text{ W} \qquad R_{L} = 8 \Omega$		0.8 0.5		A
T <sub>sd</sub>	Thermal shut-down junction temperature			145		°C
T <sub>sd</sub>	(*) Thermal shut-down case temperature	P <sub>tot</sub> = 10.5 W		120		°C

(\*) See fig. 14.

Fig. 1 - Output power vs. supply voltage

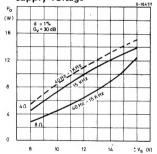


Fig. 2 - Output power vs.

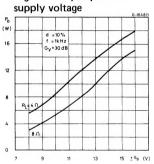


Fig. 3 - Distortion vs. output

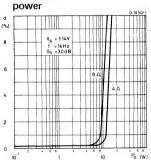


Fig. 4 - Distortion vs. output power ( $R_L = 4 \Omega$ )

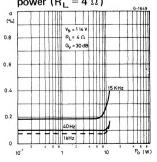


Fig. 5 - Distortion vs. output

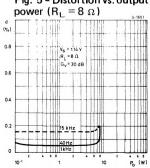


Fig. 6 - Distortion vs. frequency

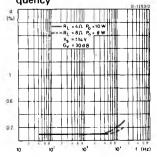


Fig. 7 - Output power vs. frequency

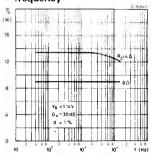


Fig. 8 - Sensitivity vs. output power ( $R_L = 4 \Omega$ )

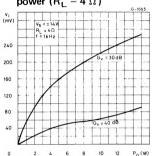


Fig. 9 - Sensitivity vs. output power ( $R_L = 8 \Omega$ )

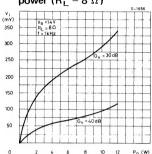


Fig. 10 - Open loop frequency response with different values of the rolloff capacitor C4

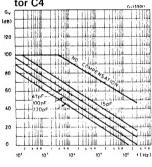


Fig. 11 - Value of C4 vs. voltage gain for different bandwidths

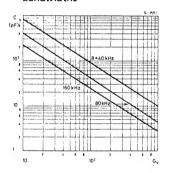


Fig. 12 - Quiescent current vs. supply voltage

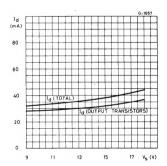


Fig. 13 - Supply voltage rejection vs. voltage gain

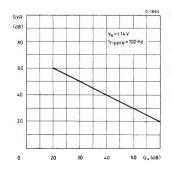


Fig. 14 - Power dissipation and efficiency vs. output power

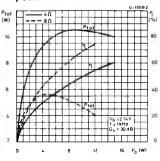
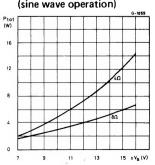


Fig. 15 - Maximum power dissipation vs. supply voltage (sine wave operation)





## **APPLICATION INFORMATION**

Fig. 16 - Application circuit with split power supply

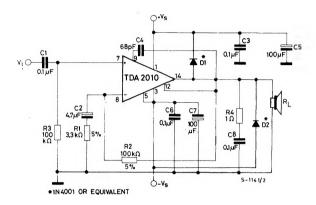
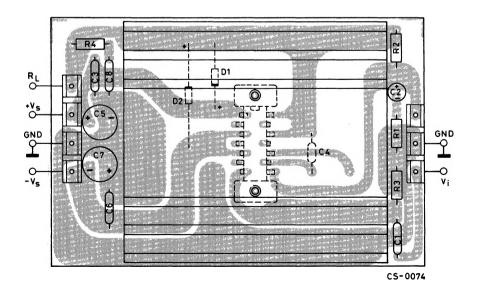


Fig. 17 - P.C. board and component layout for the circuit of fig. 16 (1:1 scale)



### SHORT CIRCUIT PROTECTION

The most important innovation in the TDA 2010 is an original circuit which limits the current of the output transistors. Fig. 18 shows that the maximum output current is a function of the collector-emitter voltage; hence the output transistors work within their safe operating area (fig. 19). This function can therefore be considered as being peak power limiting rather than simple current limiting. The TDA 2010 is thus protected against temporary overloads or short circuit. Should the short circuit exists for a longer time, the thermal shut-down comes into action and keeps the junction temperature within safe limits.

Fig. 18 - Maximum output current vs. voltave (V<sub>CE</sub>) across each output transistor

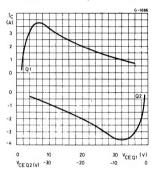
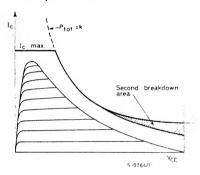


Fig. 19 - Safe operating area and collector characteristics of the protected power transistor.



### THERMAL SHUT-DOWN

The presence of a thermal limiting circuit offers the following advantages:

- 1) an overload on the output (even if it is permanent), or an above-limit ambient temperature can be easily supported since the T<sub>i</sub> cannot be higher than 150°C
- 2) the heatsink can have a smaller factor of safety compared with that of a conventional circuit. There is no possibility of device damage due to high junction temperature.
- If, for any reason, the junction temperature increases up to 150°C, the thermal shut-down simply reduces the power dissipation and the current consumption.

Fig. 20 - Output power and drain current vs. case temperature (R. = 8.0)

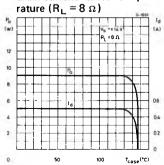
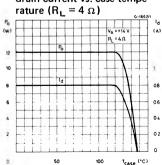


Fig. 21 - Output power and drain current vs. case temperature (R = 4.0)



### MOUNTING INSTRUCTIONS

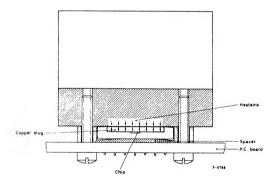
The power dissipated in the circuit must be removed by adding an external heatsink as shown in figs. 22 and 23.

The system for attaching the heatsink is very simple: it uses a plastic spacer which is supplied with the device.

Thermal contact between the copper slug (of the package) and the heatsink is guaranteed by the pressure which the screws exert via the spacer and the printed circuit board; this is due to the particular shape of the spacer.

Note: The most negative supply voltage is connected to the copper slug, hence to the heatsink (because it is in contact with the slug).

Fig. 23 - Cross-section of mounting system



The maximum allowable power dissipation depends upon the size of the external heatsink (i.e. its thermal resistance); fig. 24 shows this dissipable power as a function of ambient temperature for different thermal resistance.

Fig. 22 - Mounting system of TDA 2010

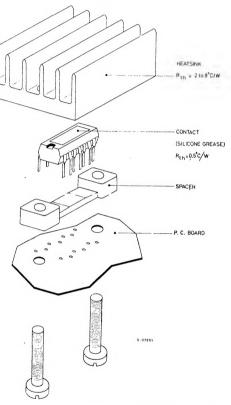


Fig. 24 - Maximum allowable power dissipation vs. ambient temperature

